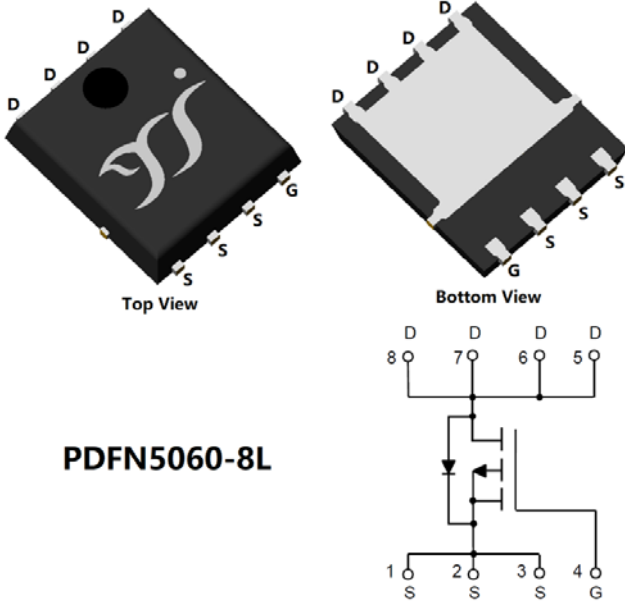


## P-Channel Enhancement Mode Field Effect Transistor



PDFN5060-8L

### Product Summary

- $V_{DS}$  -30V
- $I_D$  -70A
- $R_{DS(ON)}$ ( at  $V_{GS}=-10V$ ) <5.5mohm
- $R_{DS(ON)}$ ( at  $V_{GS}=-4.5V$ ) <9.5mohm
- 100% EAS Tested
- 100%  $\nabla V_{DS}$  Tested

### General Description

- Trench Power LV MOSFET technology
- High density cell design for Low  $R_{DS(ON)}$
- High Speed switching
- Moisture Sensitivity Level 3
- Epoxy Meets UL 94 V-0 Flammability Rating
- Halogen Free

### Applications

- Battery management
- Load switch
- Power management

### ■ Absolute Maximum Ratings ( $T_A=25^\circ C$ unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-source Voltage		$V_{DS}$	-30	V
Gate-source Voltage		$V_{GS}$	$\pm 25$	V
Drain Current	$T_C=25^\circ C$	$I_D$	-70	A
	$T_C=100^\circ C$		-44	
Pulsed Drain Current <sup>A</sup>		$I_{DM}$	-280	A
Total Power Dissipation	$T_C=25^\circ C$	$P_D$	89	W
	$T_C=100^\circ C$		36	
Total Power Dissipation	$T_A=25^\circ C$	$P_D$	7.4	W
Single Pulse Avalanche Energy <sup>B</sup>		$E_{AS}$	360	mJ
Thermal Resistance Junction-to-Case <sup>C</sup>		$R_{\theta JC}$	1.4	$^\circ C/W$
Thermal Resistance Junction-to-Ambient <sup>C</sup>		$R_{\theta JA}$	17	$^\circ C/W$
Junction and Storage Temperature Range		$T_J, T_{STG}$	-55~+150	$^\circ C$

### ■ Ordering Information (Example)

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
YJG70P03A	F1	YJG70P03A	5000	10000	100000	13" reel



# YJG70P03A

## ■ Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
<b>Static Parameter</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> =-250μA	-30			V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-30V, V <sub>GS</sub> =0V	T <sub>J</sub> =25°C		-1	μA
			T <sub>J</sub> =55°C		-5	
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = ±25V, V <sub>DS</sub> =0V			±100	nA
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> =-250μA	-1.2	-1.8	-2.8	V
Static Drain-Source On-Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = -10V, I <sub>D</sub> =-20A		4.0	5.5	mΩ
		V <sub>GS</sub> = -4.5V, I <sub>D</sub> =-20A		6.0	9.5	
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =-20A, V <sub>GS</sub> =0V			-1.2	V
Maximum Body-Diode Continuous Current	I <sub>S</sub>				-70	A
<b>Dynamic Parameters</b>						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =-15V, V <sub>GS</sub> =0V, f=1MHZ		6464		pF
Output Capacitance	C <sub>oss</sub>			779		
Reverse Transfer Capacitance	C <sub>rss</sub>			477		
Gate Resistance	R <sub>g</sub>	Drain open, f=1Mhz		6.5		Ω
<b>Switching Parameters</b>						
Total Gate Charge	Q <sub>g</sub>	V <sub>GS</sub> =-10V, V <sub>DS</sub> =-15V, I <sub>D</sub> =-20A		111.7		nC
Gate-Source Charge	Q <sub>gs</sub>			21.1		
Gate-Drain Charge	Q <sub>gd</sub>			22.9		
Reverse Recovery Charge	Q <sub>rr</sub>	I <sub>F</sub> =-15A, di/dt=-100A/us		8.5		ns
Reverse Recovery Time	t <sub>rr</sub>			24		
Turn-on Delay Time	t <sub>D(on)</sub>	V <sub>GS</sub> = -10V, V <sub>DD</sub> = -15V, R <sub>G</sub> =3Ω, R <sub>L</sub> = 0.75Ω		15		ns
Turn-on Rise Time	t <sub>r</sub>			75		
Turn-off Delay Time	t <sub>D(off)</sub>			130		
Turn-off fall Time	t <sub>f</sub>			80		

A. Pulse Test: Pulse Width≤300us, Duty cycle ≤2%.

B. T<sub>J</sub>=25°C, V<sub>DD</sub>=-25V, V<sub>G</sub>=-10V, L=2mH, I<sub>AS</sub>=-19A.

C. R<sub>θJA</sub> is the sum of the junction-to-case and case-to-ambient thermal resistance, where the case thermal reference is defined as the soldermounting surface of the drain pins. R<sub>θJC</sub> is guaranteed by design, while R<sub>θJA</sub> is determined by the board design. The maximum rating presented here is based on mounting on a 1 in 2 pad of 2oz copper.



■ Typical Performance Characteristics

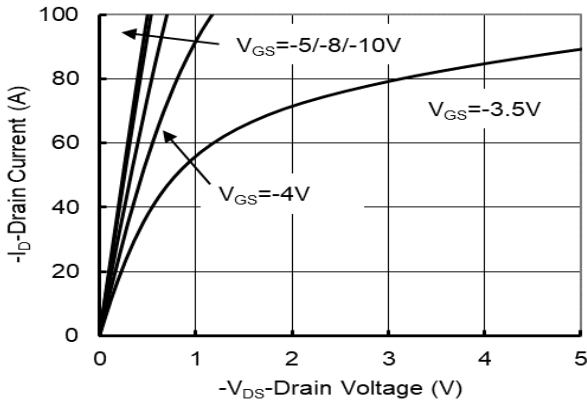


Figure1. Output Characteristics

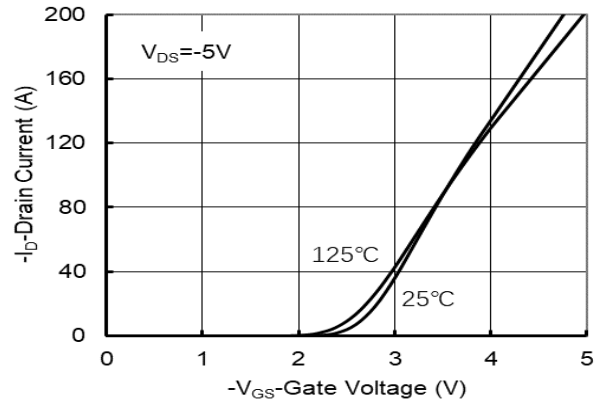


Figure2. Transfer Characteristics

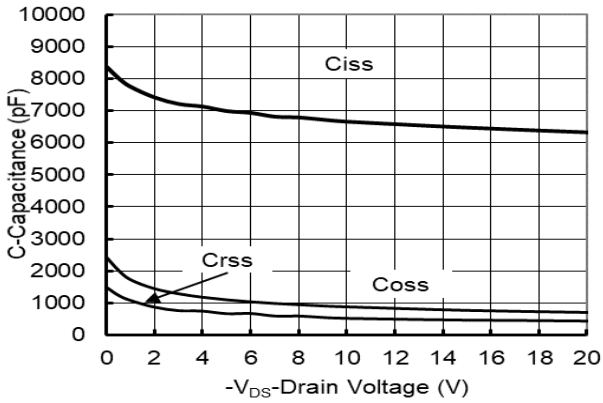


Figure3. Capacitance Characteristics

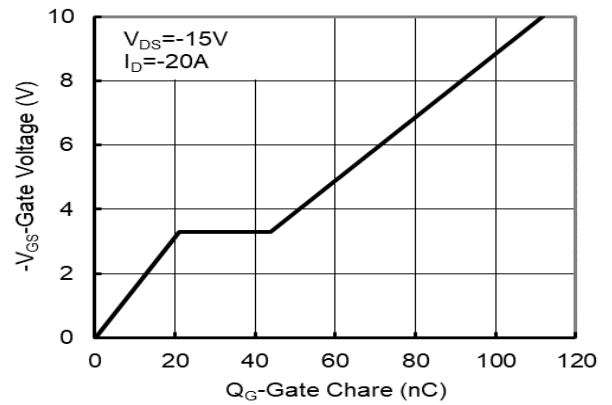


Figure4. Gate Charge

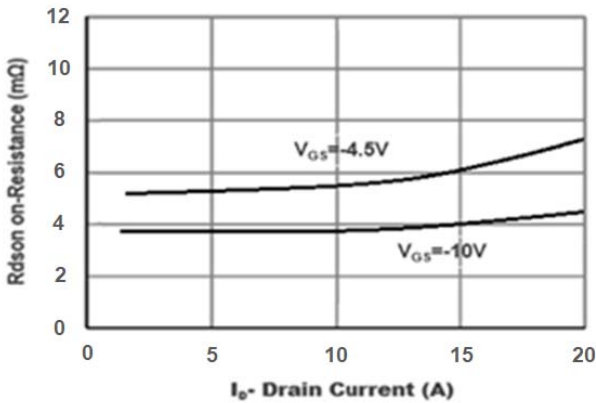


Figure5. Drain-Source on Resistance

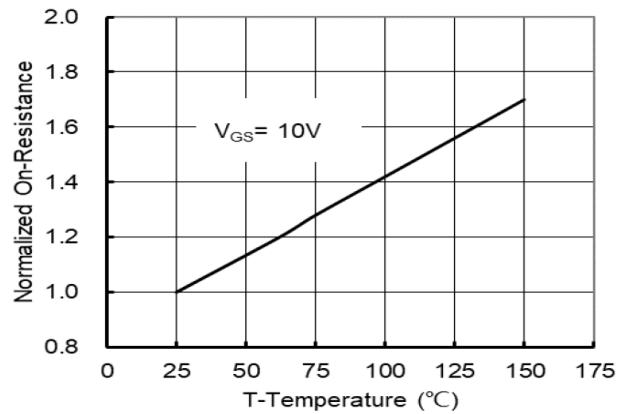


Figure6. Drain-Source on Resistance



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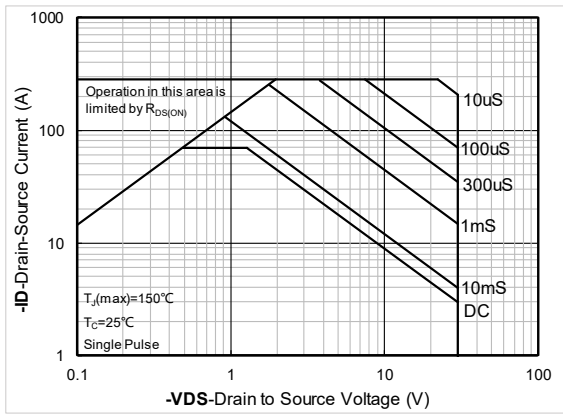


Figure7. Safe Operation Area

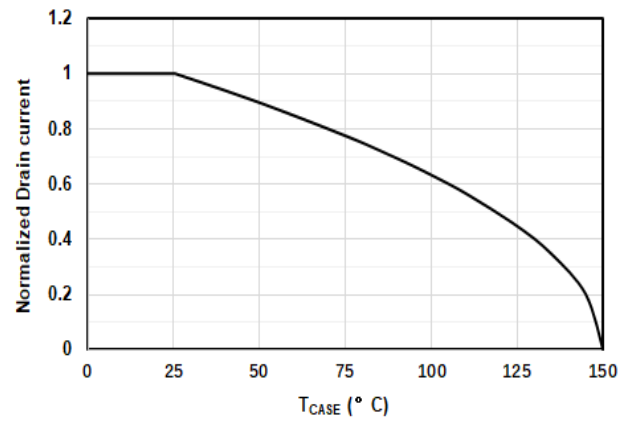


Figure8. Drain current vs. Case Temperature

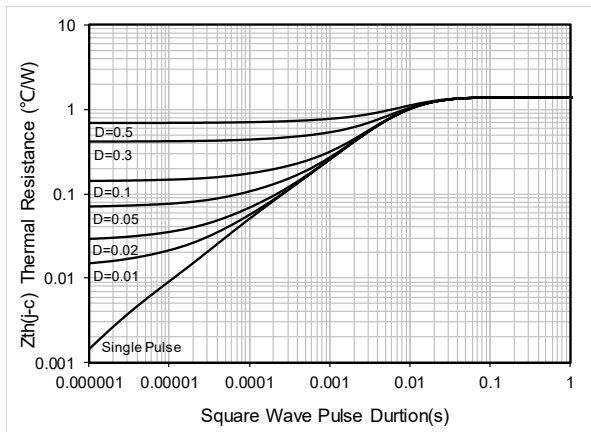
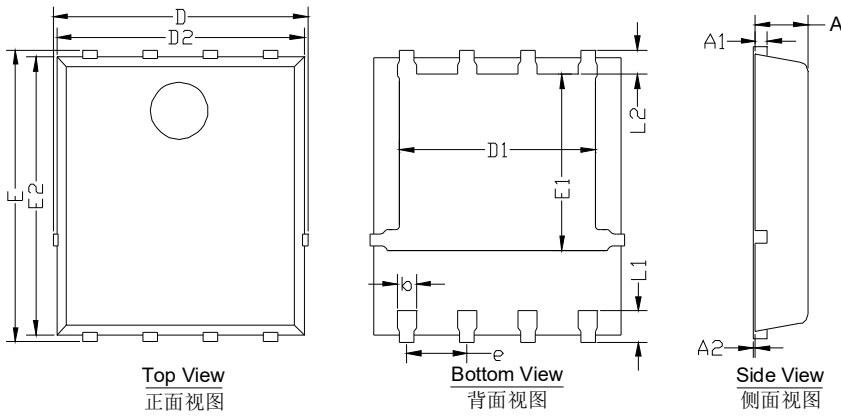


Figure9. Normalized Maximum Transient Thermal Impedance

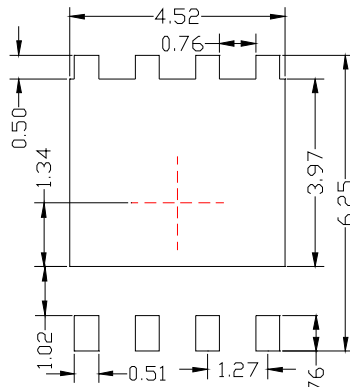


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## ■ PDFN5060-8L Package information



SYMBOL	MILLIMETER		
	MIN	NOM	MAX
D	5.15	5.35	5.55
E	5.95	6.15	6.35
A	1.00	1.10	1.20
A1	0.254 BSC		
A2			0.10
D1	3.92	4.12	4.32
E1	3.52	3.72	3.92
D2	5.00	5.20	5.40
E2	5.66	5.86	6.06
L1	0.56	0.66	0.76
L2	0.50 BSC		
b	0.31	0.41	0.51
e	1.27 BSC		



- Note:
1. Controlling dimension: in millimeters.
  2. General tolerance:  $\pm 0.10$ mm.
  3. The pad layout is for reference purposes only.



## YJG70P03A

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